

22. (Amended) The method of Claim 16, wherein n-doped or p-doped areas for the creation of the structures forming the semiconductor components are produced in the active areas.

25. (Amended) The method of Claim 1 employed for the creation of a structure forming a photosensitive transistor in which an n-doped area is implanted into the p-doped inner area, whereby the terminal forming the collector at the fringe area of the n-doped trough and the terminal forming the emitter at the n-doped area implanted into the p-doped inner area is created.

26. (Amended) The method of Claim 1, wherein the p-doped or the n-doped semiconductor substrate is a weakly p-doped or n-doped semiconductor substrate.



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